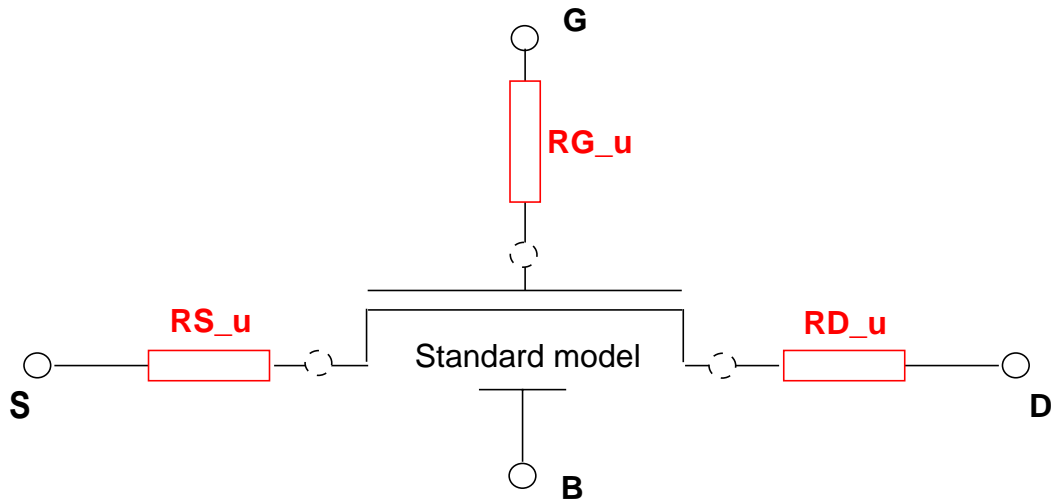


RPO MOS TRANSISTOR MODELS

1. PRINCIPLE

RPO MOS transistor model is a subcircuit based on standard model.

Three voltage independent resistances have been added on Gate node, Drain node and Source node.



2. APPLICATION

This model is dedicated to unsalicyded MOS transistors for IO applications.

3. NOMENCLATURE

RPO's model names are standard model names ended by "RPO" extension.

- Example: NLVTLP RPO for Low Threshold Voltage LP NMOS

Two new instance parameters have been added in order to define unsalicyded area dimensions: **esu** and **edu** (see schema below).

- Example:

XM1 D G S B NLVTLP RPO W=10 L= 0.5 **esu = 0.3 edu = 0.3**

